2SK2339

Silicon N-Channel Power F-MOS

■ Features

- Avalanche energy capability guaranteed
- Low ON-resistance
- No secondary breakdown
- Low-voltage drive

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

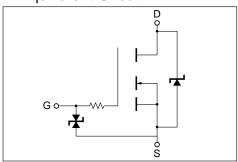
■ Absolute Maximum Ratings (Tc = 25°C)

Parameter		Symbol	Rating	Unit	
Drain-Source breakdown voltage		V _{DSS}	80±10	V	
Gate-Source voltage		V _{GSS}	±15	V	
Drain current	DC	I_D	±10	A	
	Pulse	I _{DP}	±20	A	
Avalanche energy capability		EAS*	62.5	mJ	
Allowable power dissipation	$T_C = 25^{\circ}C$	D	30	W	
	Ta= 25°C	$P_{\rm D}$	1.3		
Channel temperature		T _{ch}	150	°C	
Storage temperature		T _{stg}	-55 to +150	°C	

^{*} L= 5mH, I_L = 5A, 1 pulse

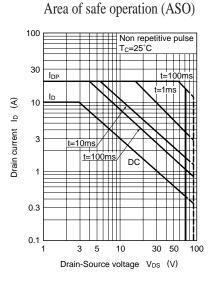
Unit: mm 3.4±0.3 8.5±0.2 6.0±0.5 1.0±0.1 10.0±0.3 1.5±0.1 1.5max. 1.1max. 0.8±0.1 0.5max. 2.54±0.3 1: Gate 2 : Collector 3: Emitter N Type Package

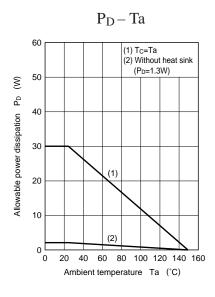
■ Equivalent Circuit

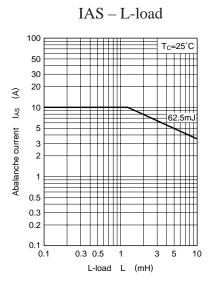


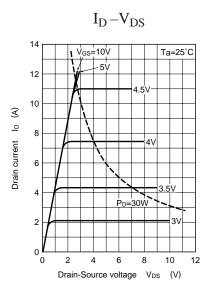
■ Electrical Characteristics (Tc = 25°C)

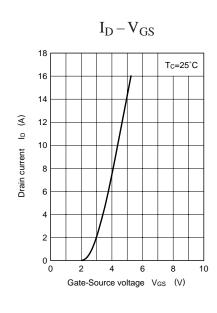
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source cut-off current	I _{DSS}	$V_{DS} = 70V, V_{GS} = 0$			10	μΑ
Gate-Source leakage current	I _{GSS}	V _{DS} = 0, V _{GS} =15V			±10	μΑ
Drain-Source breakdown voltage	V _{DSS}	$I_D=1$ mA, $V_{GS}=0$	70		90	V
Gate threshold voltage	V _{th}	V _{DS} =10V, I _D =1mA	1		2.5	V
Drain-Source ON-resistance	R _{DS(on)} 1	V _{GS} =10V, I _D = 5A		150	230	mΩ
	R _{DS(on)} 2	$V_{GS}=4V$, $I_D=5A$		230	370	mΩ
Forward transadmittance	Y _{fs}	$V_{DS}=10V, I_{D}=5A$	3	5.5		S
Diode forward voltage	V _{DSF}	$I_{DR}=10A$, $V_{GS}=0$			-1.8	V
Reverse recovery time	t _{rr}	L=230 μ H, V _{DD} = 30V, V _{GS} = 0		0.55		μs
Reverse recovery charge	Qrr	I _{DR} =10A, di/dt= 80A/μ s		2.2		μs
Input capacitance	Ciss			85		pF
Output capacitance	Coss	$V_{DS}=10V, V_{GS}=0, f=1MHz$		250		pF
Feedback capacitance	C _{rss}			20		pF
Turn-on time	ton	V _{DD} = 30V, I _D = 5A		0.5		μs
Fall time	t_{f}			0.9		μs
Turn-off time (delay time)	t _{d(off)}	$V_{GS}=10V, R_{L}=6\Omega$		1.9		μs
Channel-Case heat resistance	R _{th(ch-c)}				4.2	°C/W
Channel-Atmosphere heat resistance	R _{th(ch-a)}				96	°C/W

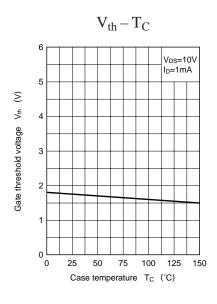


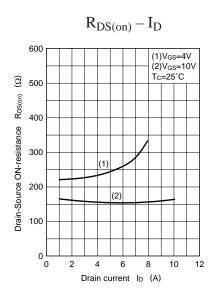


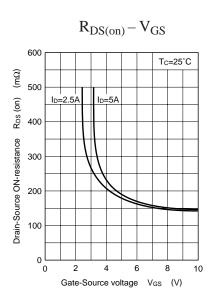


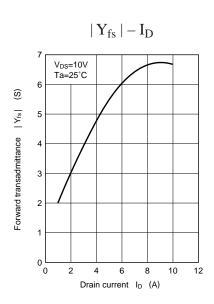




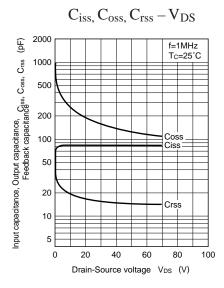


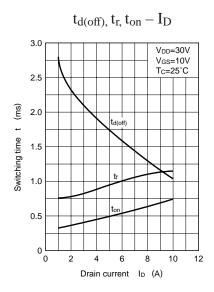


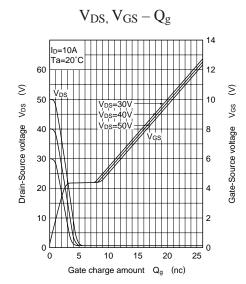


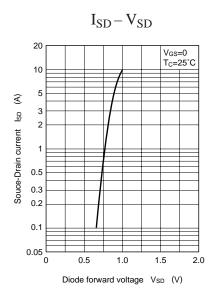


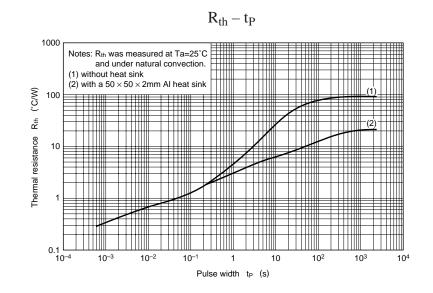
Power F-MOS FETs 2SK2339











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